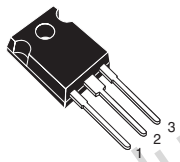
STW24NK55Z

N-channel 550 V - 0.18 Ω - 23 A - TO-247
Zener-protected SuperMESH™ Power MOSFET

Features

Type	V_{DSS}	$R_{DS(on)}$	I_D	Pw
STW24NK55Z	550 V	<0.22 Ω	23 A	285 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability



TO-247

Application

- Switching applications

Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs.

Figure 1. Internal schematic diagram

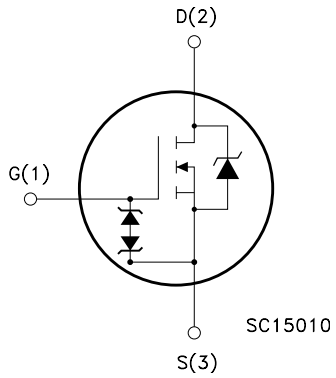


Table 1. Device summary

Order code	Marking	Package	Packaging
STW24NK55Z	24NK55Z	TO-247	Tube

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	550	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at T_C = 25 °C	23	A
I_D	Drain current (continuous) at T_C=100 °C	10.35	A
I_{DM}(1)	Drain current (pulsed)	92	A
P_{TOT}	Total dissipation at T_C = 25 °C	285	W
	Derating factor	2.27	W/°C
dv/dt(2)	Peak diode recovery voltage slope	4.5	V/ns
T_{stg}	Storage temperature	-55 to 150°C	°C
T_J	Max. perating junction temperature	150	°C

1. Pulse width limited by safe operating area
2. I_{SD} ≤ 23 A, di/dt ≤ 200 A/µs,V_{DD}= 80% $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.44	°C/W
$R_{thj\text{-}a}$	Thermal resistance junction-ambient max	50	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	23	A
E_{AS}	Single pulse avalanche energy (starting Tj=25 °C, I_D=I_{AR}, V_{DD}=50 V)	400	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS}= 0	550			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating @125 °C			1 50	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 100 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10 V, I_D= 11.5 A		0.18	0.22	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} =15 V, I_D = 11.5 A		20		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25 V, f=1 MHz, V_{GS}=0		4397.5 480.5 116		pF pF pF
$C_{oss\ eq}$ (2).	Equivalent output capacitance	V_{GS}=0, V_{DS} =0 to 480 V		250		pF
R_G	Intrinsic gate resistance	f=1 MHz, open drain		2.3		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}= 440 V, I_D = 23 A V_{GS} =10 V *(see Figure 15)*		130 25 76		nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD}= 275 V, I_D=11.5 A, R_G= 4.7 Ω, V_{GS}=10 V *(see Figure 14)*		30 35 136 88		ns ns ns ns

1. Pulsed: pulse duration=300 µs, duty cycle 1.5%
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				23	A
I_{SDM}(1)	Source-drain current (pulsed)				92	A
V_{SD}(2)	Forward on voltage	I_{SD}= 23 A, V_{GS}=0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}= 23 A, V_{DD}= 50 V di/dt = 100 A/µs, *(see Figure 18)*		508 7.4 29		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}= 23 A, di/dt = 100 A/µs, V_{DD}= 50 V, Tj=150 °C *(see Figure 18)*		608 9.7 31.8		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 µs, duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}(1)	Gate-source breakdown voltage	Igs=±1 mA (open drain)	30			V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

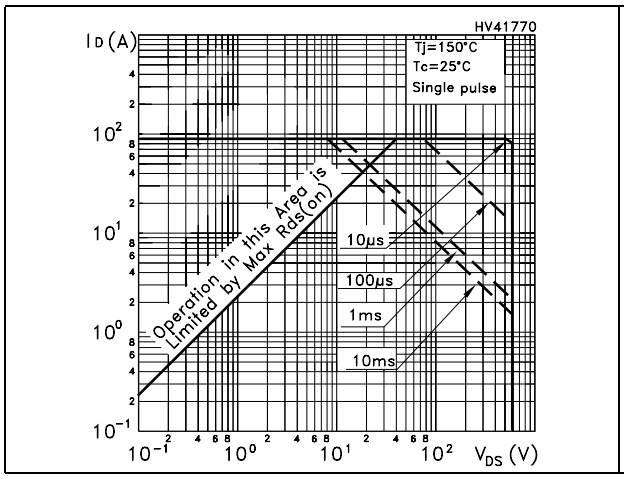


Figure 3. Thermal impedance

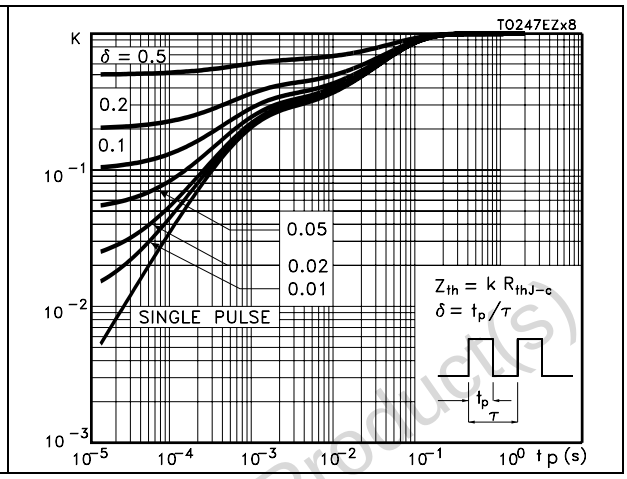


Figure 4. Output characteristics

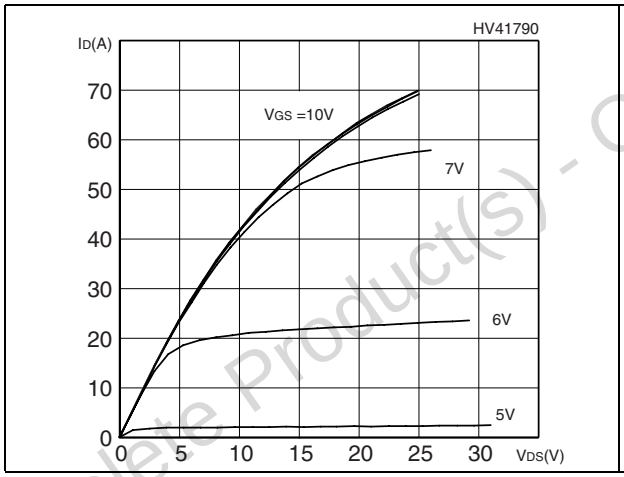


Figure 5. Transfer characteristics

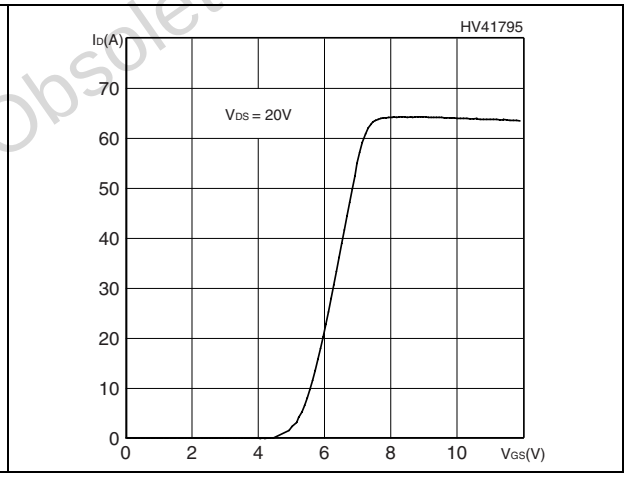


Figure 6. Normalized BV_{DSS} vs temperature

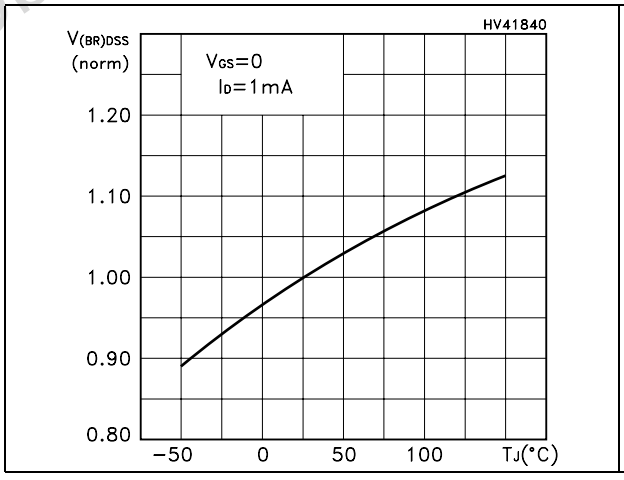


Figure 7. Static drain-source on resistance

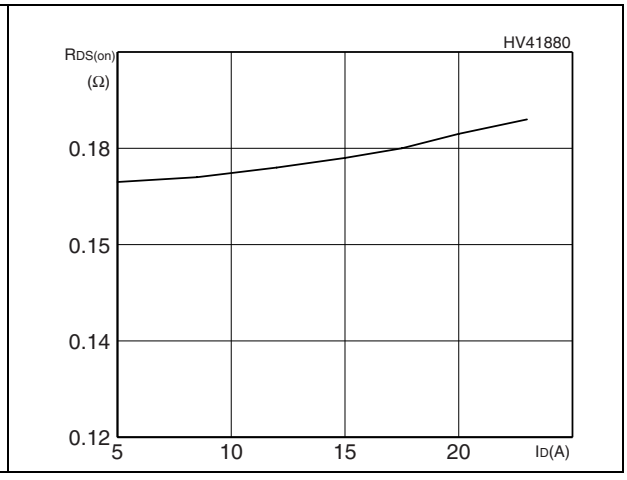


Figure 8. Gate charge vs gate-source voltage

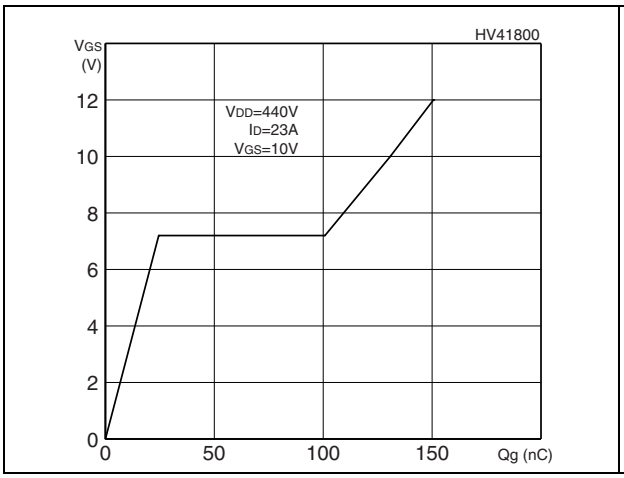


Figure 9. Capacitance variations

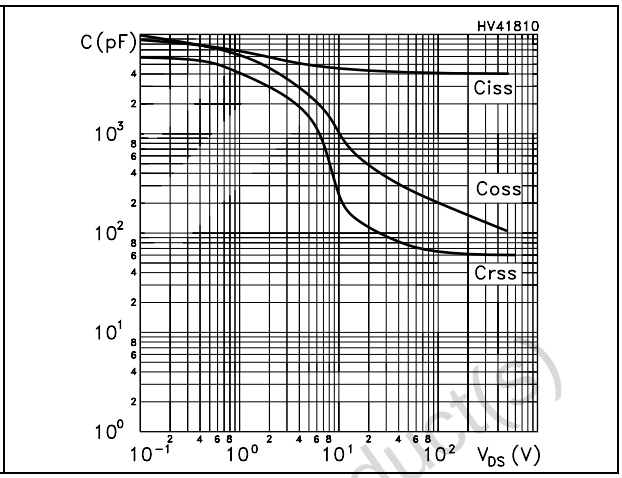


Figure 10. Normalized gate threshold voltage vs temperature

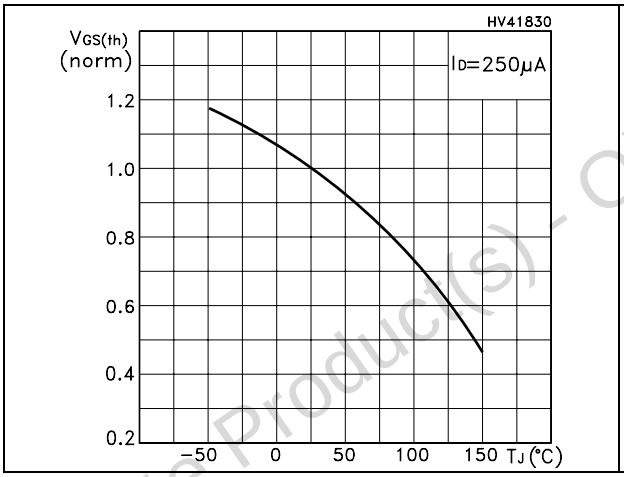


Figure 11. Normalized on resistance vs temperature

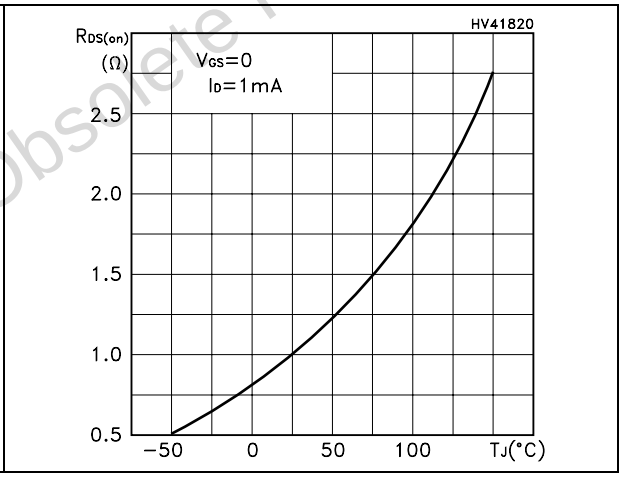


Figure 12. Maximum avalanche energy vs temperature

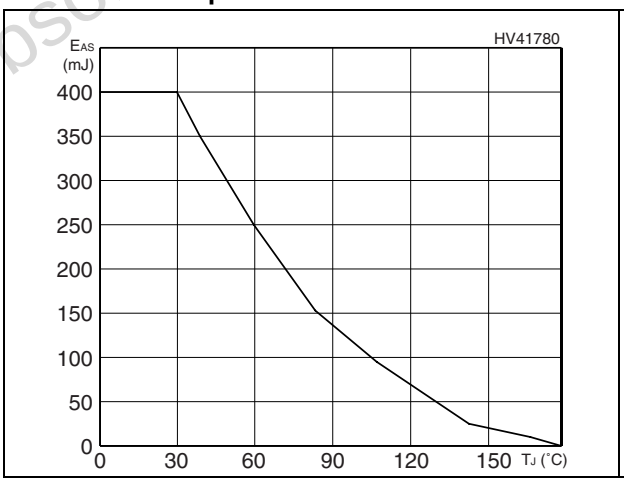
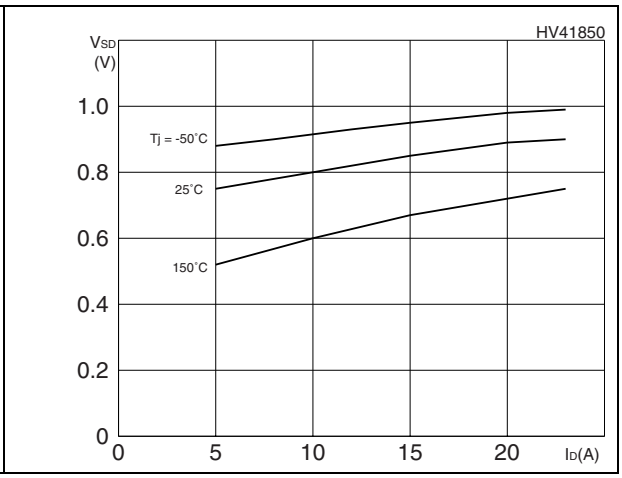


Figure 13. Source-drain diode forward characteristics



3 Test circuits

Figure 14. Switching times test circuit for resistive load

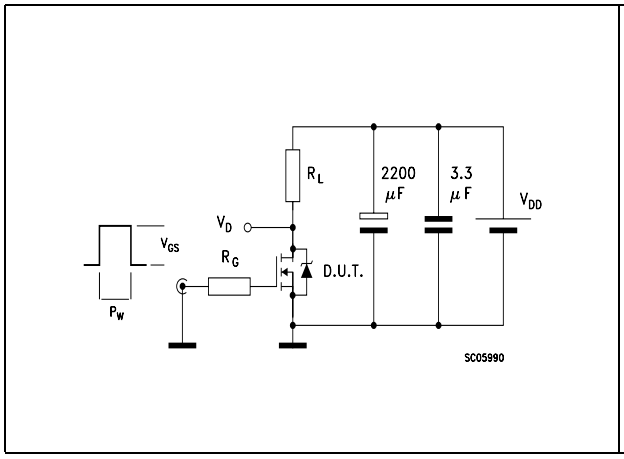


Figure 15. Gate charge test circuit

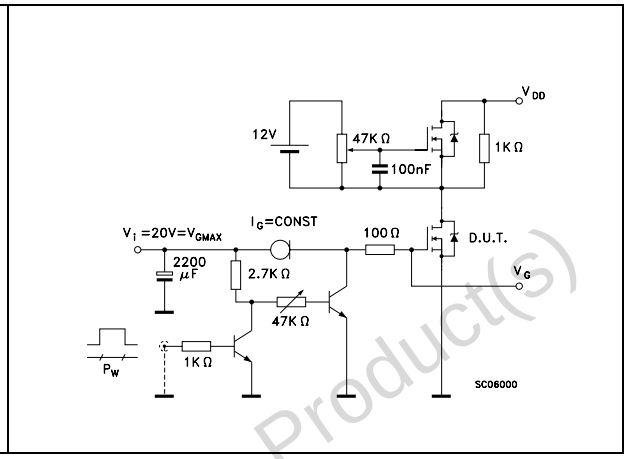


Figure 16. Test circuit for inductive load switching and diode recovery times

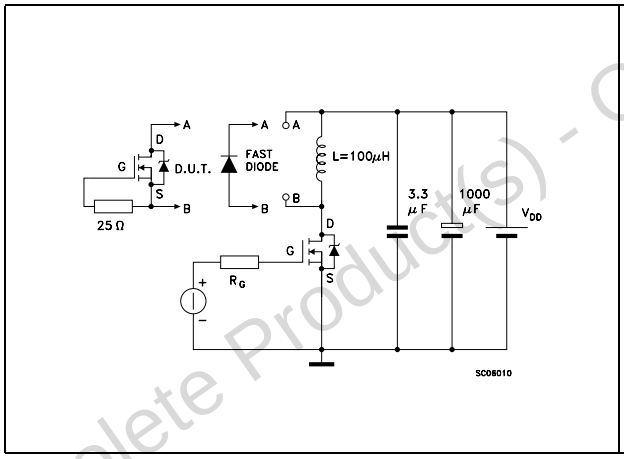


Figure 17. Unclamped Inductive load test circuit

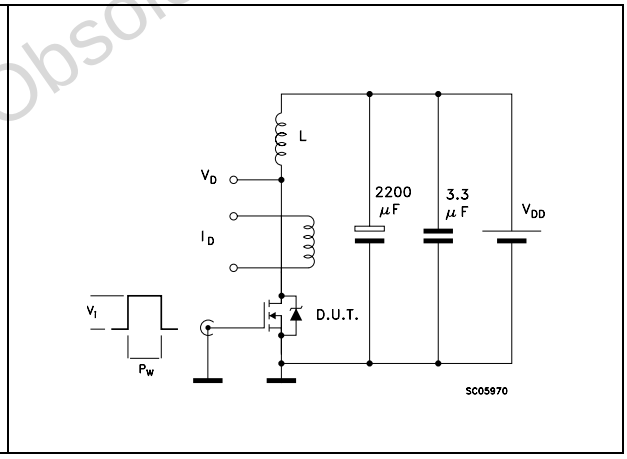


Figure 18. Unclamped inductive waveform

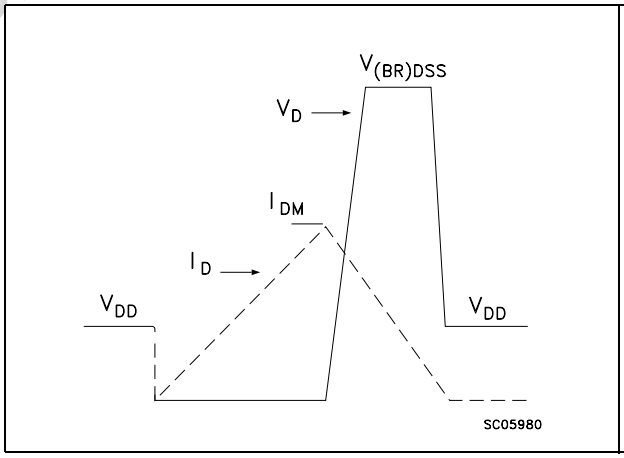
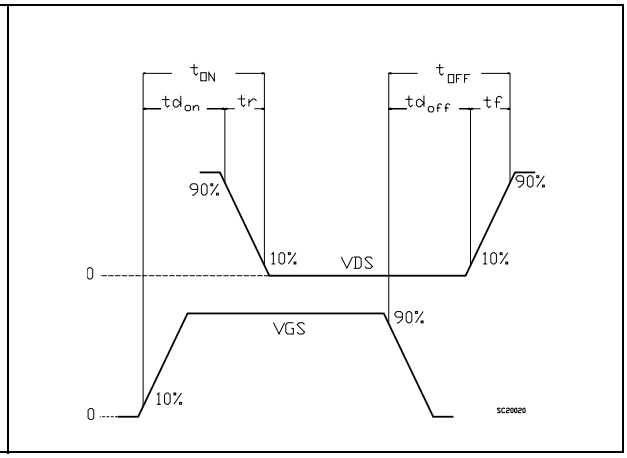


Figure 19. Switching time waveform

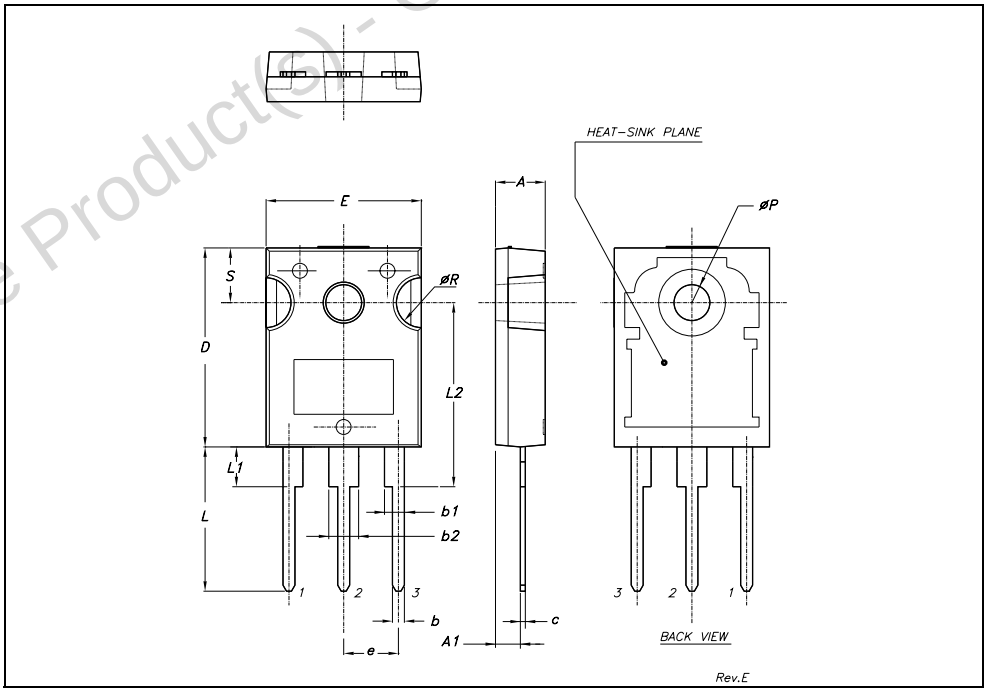


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
04-Jan-2008	1	First release

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